

### MOS FIELD EFFECT TRANSISTOR

2SK3433

# SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

### **DESCRIPTION**

The 2SK3433 is N-channel MOS Field Effect Transistor designed for high current switching applications.

### **FEATURES**

• Super low on-state resistance:

RDS(on)1 =  $26 \text{ m}\Omega$  MAX. (VGS = 10 V, ID = 20 A)

- ★ RDS(on)2 = 41 m $\Omega$  MAX. (Vgs = 4.0 V, ID = 20 A)
  - Low Ciss: Ciss = 1500 pF TYP.
  - Built-in gate protection diode

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ )

	Drain to Source Voltage	VDSS	60	V
	Gate to Source Voltage	Vgss	±20	V
	Drain Current (DC)	I <sub>D(DC)</sub>	±40	Α
	Drain Current (pulse) Note1	D(pulse)	±160	Α
*	Total Power Dissipation (Tc = 25°C)	Рт	47	W
	Total Power Dissipation (T <sub>A</sub> = 25°C)	Рт	1.5	W
	Channel Temperature	$T_ch$	150	°C
	Storage Temperature	T <sub>stg</sub>	-55 to +150	°C
*	Single Avalanche Current Note2	las	21	Α
*	Single Avalanche Energy Note2	Eas	44	mJ

**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty cycle  $\leq$  1 %

**2.** Starting T<sub>ch</sub> = 25 °C, R<sub>G</sub> = 25  $\Omega$ , V<sub>GS</sub> = 20 V  $\rightarrow$  0 V

# THERMAL RESISTANCE

★ Cl	Channel to Case	Rth(ch-C)	2.66	°C/W
	Channel to Ambient	Rth(ch-A)	83.3	°C/W

### **ORDERING INFORMATION**

PART NUMBER	PACKAGE		
2SK3433	TO-220AB		
2SK3433-S	TO-262		
2SK3433-Z	TO-220SMD		

(TO-220AB)



(TO-262)



(TO-220SMD)



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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

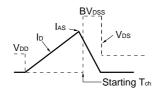


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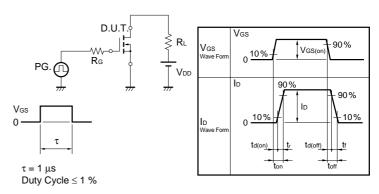
	CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Drain to Source On-state Resistance	R <sub>DS(on)1</sub>	V <sub>G</sub> S = 10 V, I <sub>D</sub> = 20 A		22	26	mΩ
*		RDS(on)2	Vgs = 4.0 V, lb = 20 A		29	41	mΩ
	Gate to Source Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.5	2.0	2.5	V
*	Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 20 A	11	22		S
	Drain Leakage Current	IDSS	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			10	μΑ
	Gate to Source Leakage Current	Igss	V <sub>G</sub> S = ±20 V, V <sub>D</sub> S = 0 V			±10	μΑ
	Input Capacitance	Ciss	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		1500		pF
	Output Capacitance	Coss			250		pF
	Reverse Transfer Capacitance	Crss			120		pF
*	Turn-on Delay Time	td(on)	ID = 20 A, VGS(on) = 10 V, VDD = 30 V,		35		ns
*	Rise Time	tr	R <sub>G</sub> = 10 Ω		320		ns
*	Turn-off Delay Time	td(off)			89		ns
*	Fall Time	tf			120		ns
	Total Gate Charge	Q <sub>G</sub>	ID = 40 A , VDD = 48 V, VGS = 10 V		30		nC
	Gate to Source Charge	Qgs			5		nC
	Gate to Drain Charge	<b>Q</b> GD			8		nC
	Body Diode Forward Voltage	V <sub>F(S-D)</sub>	IF = 40 A, Vgs = 0 V		1.0		V
*	Reverse Recovery Time	trr	IF = 40 A, Vgs = 0 V,		44		ns
*	Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		60		nC

### **TEST CIRCUIT 1 AVALANCHE CAPABILITY**

# $\begin{array}{c|c} D.U.T. \\ \hline R_G = 25 \ \Omega \\ \hline PG. \\ \hline V_{GS} = 20 \rightarrow 0 \ V \end{array} \begin{array}{c} D.U.T. \\ \hline \end{array} \begin{array}{c} \\ \end{array} \end{array} \begin{array}{c} \\ \end{array} \end{array} \begin{array}{c} \\ \end{array} \end{array} \begin{array}{c} \\ \end{array} \end{array} \begin{array}{c} \\ \end{array} \end{array} \begin{array}{c} \\ \end{array} \end{array} \begin{array}{c} \\ \end{array} \end{array} \begin{array}{c} \\ \end{array} \end{array} \begin{array}{c} \\ \end{array} \end{array} \begin{array}{c} \\ \end{array} \begin{array}{c} \\ \end{array} \begin{array}{c} \\ \end{array} \begin{array}{c} \\ \end{array} \end{array} \begin{array}{c} \\ \end{array} \begin{array}{c} \\$



### **TEST CIRCUIT 2 SWITCHING TIME**



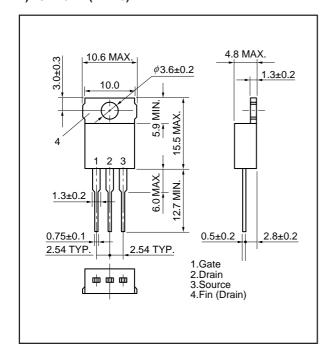
### **TEST CIRCUIT 3 GATE CHARGE**

$$\begin{array}{c|c} \text{D.U.T.} \\ \text{Ig} = 2 \text{ mA} \\ \text{W-o} \end{array} \begin{array}{c} \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \end{array} \begin{array}{c}$$

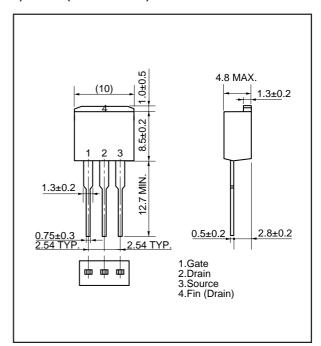


## 章ACKAGE DRAWINGS (Unit: mm)

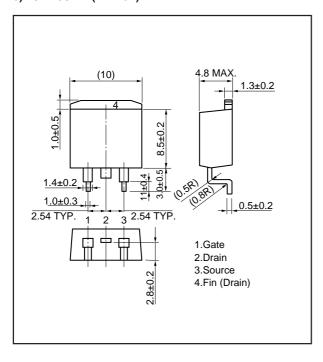
### 1) TO-220AB (MP-25)



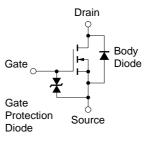
### 2) TO-262 (MP-25 Fin Cut)



### 3) TO-220SMD (MP-25Z)



### **EQUIVALENT CIRCUIT**



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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